



a step in which the processing gas is raised to plasma; and

4. A plasma processing method in which a photoresist film with an opening pattern having an opening area larger than the opening area of a hole formed at a specific layer of a workpiece and containing the opening of said hole is used as a mask to implement a plasma etching process halfway through said specific layer and then said photoresist film is removed, comprising:

a step in which the processing gas is raised to plasma; and

5. A plasma processing method according to any of claims 1 ~ 4, wherein:

6. A plasma processing method according to any of claims 1 ~ 4, wherein:

